

MDJ178 37-61 GHz InP Schottky Diode Mixer

#### **PRODUCT DESCRIPTION**

The MDJ178 is a Q & V-Band monolithic InP Schottky diode, double balanced mixer designed for use in commercial digital radios, wireless LANs. Radar, Satcom & Test Equipment. The design requires no external bias and can be used as an upconverter and as a downconverter. To ensure rugged and reliable operation, the InP Schottky devices are fully passivated. Both bond pad and backside metallization are Ti/Au, which is compatible with conventional die attach, thermocompression, and thermosonic wire bonding assembly techniques.

#### **APPLICATIONS**

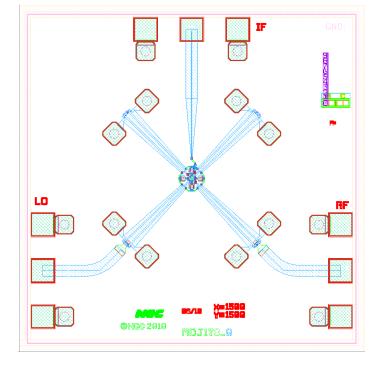
- · Point-to-Point Digital Radios
- Point-to-Multipoint Digital Radios
- Short Haul / High-Capacity Links
- Wireless LANs
- SatCom
- · Test equipment and sensors
- Military & Space Applications

#### **PRODUCT FEATURES**

- Passive Double Balanced Mixer
- RF/LO: 37-61 GHz
- IF: DC-15 GHz (min)
- Downconverter Conversion Loss < 8.5 dB</li>
- LO Input Power 9 dBm (Typ)
- RF & LO ports are interchangeable.
- Chip Size: 1.5 mm x 1.5 mm

#### www.ngc.com

www.ngc.com/what-we-do/microelectronics-space-park/ Phone: (310) 814-5000 • Fax: (310) 812-7011 • E-mail: as-mps.sales@ngc.com Approved for Public Release: NG23-2498. © 2023 Northrop Grumman Systems Corporation



X=1.5 mm; y=1.5 mm

#### **EXPORT INFORMATION**

ECCN: 5A991.h

HTS (Schedule B) code: 8542.39





# MDJ178 37 – 61 GHz InP Schottky Diode Mixer ABSOLUTE MAXIMUM RATINGS

#### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Value	Unit
Input LO Power	14	dBm
Assy. Temperature (30		
sec)	300	°C

Parameter	Value	Unit
Input LO Power	8-12	dBm

#### **ELECTRICAL SPECIFICATIONS**

Parameter	Min	Typical	Max	Unit		
Operational LO Frequency	37		61	GHZ		
Operational RF Frequency	37		61	GHZ		
Operational IF Frequency	DC		15	GHZ		
Performance @ LO Power = 9 dBm						
DownConverter Conversion Loss			8.5	dB		
UpConverter Conversion Loss			7.5	dB		
RF to LO Isolation		20		dB		

www.ngc.com/what-we-do/microelectronics-space-park/ Phone: (310) 814-5000 • Fax: (310) 812-7011 • E-mail: as-mps.sales@ngc.com Approved for Public Release: NG23-2498. © 2023 Northrop Grumman Systems Corporation

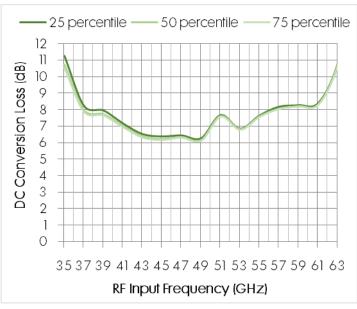


## **MDJ178** 37 - 61 GHz

IF=1.1 GHz

**InP Schottky Diode Mixer** On-wafer measured Downconverter Performance Characteristics (Typical Performance at 25°C)

## **Conversion Loss vs. Frequency**



<sup>\*</sup> LO Power = 9dBm



www.ngc.com

www.ngc.com/what-we-do/microelectronics-space-park/ Phone: (310) 814-5000 • Fax: (310) 812-7011 • E-mail: as: mps.sales@ngc.com Approved for Public Release: NG23-2498. © 2023 Northrop Grumman Systems Corporation



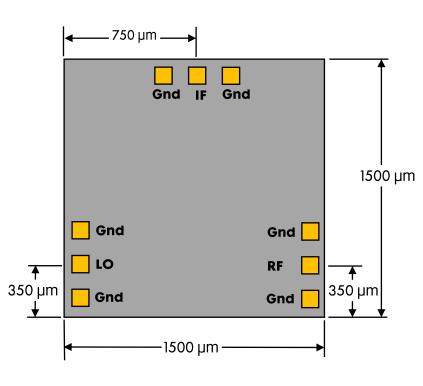
### MDJ178 37 – 61 GHz InP Schottky Diode Mixer

#### **DIE SIZE AND BOND PAD LOCATIONS (NOT TO SCALE)**

 $X = 1500 \pm 25 \mu m$   $Y = 1500 \pm 25 \mu m$ RF Bond Pad = 100 x 100 ± 0.5 μm Chip Thickness = 76 ± 5 μm

#### RECOMMENDED ASSEMBLY NOTES

1. Best performance obtained from use of <10 mil (long) by 3 by 0.5 mil ribbon on Ports.



#### **MOUNTING PROCESSES**

Most NG InP IC chips have a gold backing and can be mounted successfully using either a conductive epoxy or AuSn attachment. NG recommends the use of conductive epoxy due to the reduced mechanical strain placed on the chip. The two most important factors when mounting these MMICs are to provide a good thermal path and a good RF path to ground. This should be considered when determining the method for attachment.

Note: Many of the NG parts do incorporate airbridges, so caution should be used when determining the pick up tool.

CAUTION: THE IMPROPER USE OF AuSn ATTACHMENT CAN CATASTROPHICALLY DAMAGE InP CHIPS.

PLEASE ALSO REFER TO OUR "GaAs & InP Application Note" BEFORE HANDLING, ASSEMBLING OR BIASING THESE MMICS!

Page 4

www.ngc.com

www.ngc.com/what-we-do/microelectronics-space-park/ Phone: (310) 814-5000 • Fax: (310) 812-7011 • E-mail: as-mps.sales@ngc.com Approved for Public Release: NG23-2498. © 2023 Northrop Grumman Systems Corporation

